NCE N-Channel Enhancement Mode Power MOSFET

Description

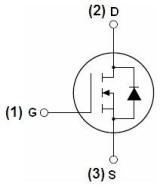
The NCEA6080K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

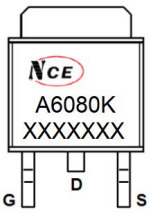
- V_{DS} =60V,I_D =80A
  $R_{DS(ON)}$ <7.9mΩ @ V_{GS}=10V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- 100% UIS tested
- 100% ΔVds tested
- **AEC-Q101 qualified**

Application

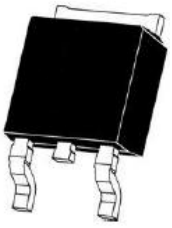
- Automotive application
- PWM
- Load Switching



Schematic diagram



Marking and pin assignment



TO-252-2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
A6080K	NCEA6080K	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	80	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	56.5	A
Pulsed Drain Current	I_{DM}	320	A
Maximum Power Dissipation	P_D	110	W
Derating factor		0.73	W/℃
Single pulse avalanche energy (Note 1)	E_{AS}	390	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 175	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	1.36	℃/W
Thermal Resistance,Junction-to-Ambient(Note 4)	$R_{\theta JA}$	60	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	2	2.8	4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=20A	-	6.2	7.9	mΩ
Forward Transconductance	g_{FS}	V_{DS}=10V,I_D=20A	-	40	-	S
Dynamic Characteristics						
Input Capacitance	C_{lss}	V_{DS}=30V,V_{GS}=0V, F=1.0MHz	-	4000	-	pF
Output Capacitance	C_{oss}		-	290	-	pF
Reverse Transfer Capacitance	C_{rss}		-	210	-	pF
Switching Characteristics (Note 2)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=30V,R_L=1Ω V_{GS}=10V,R_G=3Ω	-	8.5	-	nS
Turn-on Rise Time	t_r		-	7	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	40	-	nS
Turn-Off Fall Time	t_f		-	15	-	nS
Total Gate Charge	Q_g	V_{DS}=30V,I_D=20A, V_{GS}=10V	-	83	-	nC
Gate-Source Charge	Q_{gs}		-	19.5	-	nC
Gate-Drain Charge	Q_{gd}		-	23.4	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	V_{GS}=0V,I_S=20A	-	-	1.2	V
Diode Forward Current	I_S		-	-	80	A
Reverse Recovery Time	t_{rr}	TJ = 25°C, IF = 20A di/dt = 100A/μs	-	32	-	nS
Reverse Recovery Charge	Qrr		-	45	-	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. EAS condition : Tj=25℃,V_{DD}=30V,V_G=10V,L=0.5mH,Rg=25Ω
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_J(MAX)=175°C. The SOA curve provides a single pulse rating.
4. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The value in any given application depends on the user's specific board design.

Typical Electrical and Thermal Characteristics (Curves)

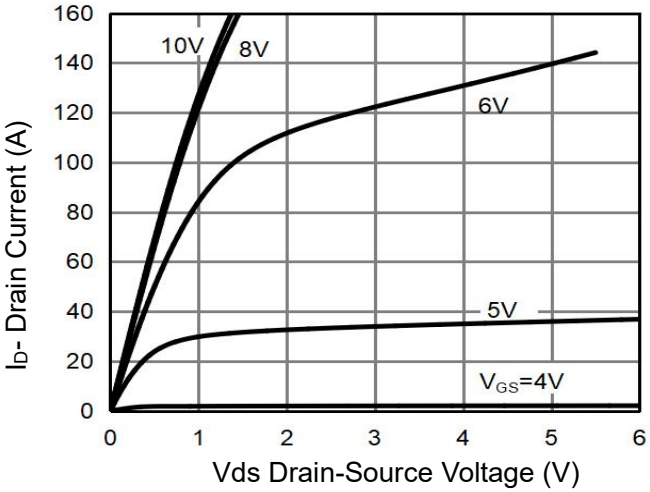


Figure 1 Output Characteristics

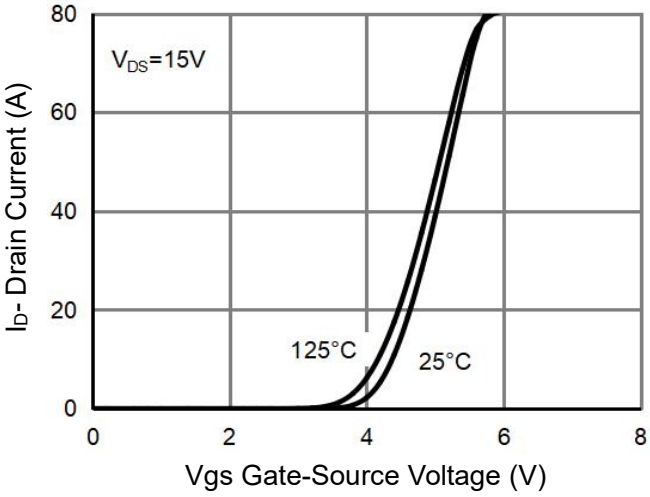


Figure 2 Transfer Characteristics

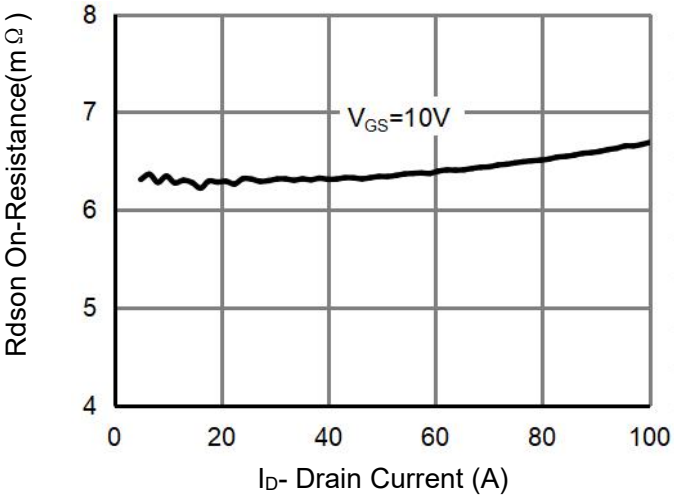


Figure 3 Rdson- Drain Current

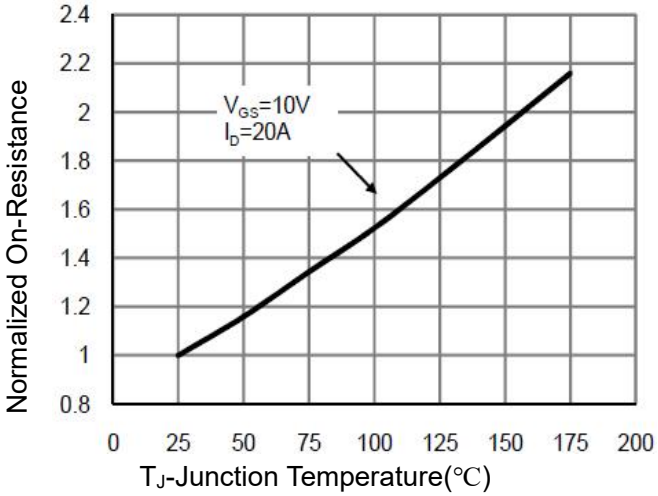


Figure 4 Rdson-JunctionTemperature

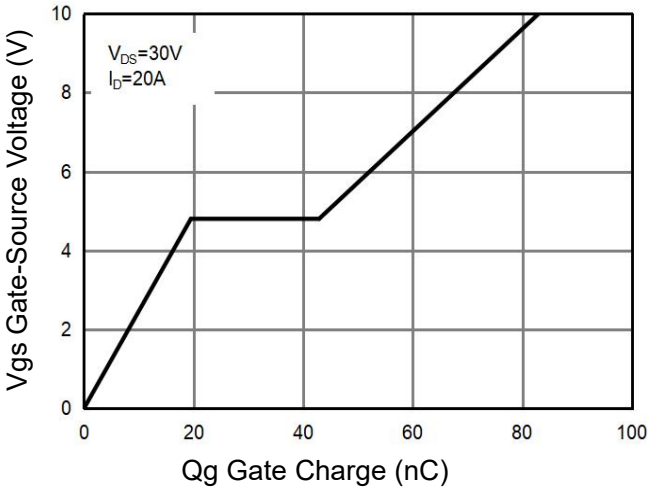


Figure 5 Gate Charge

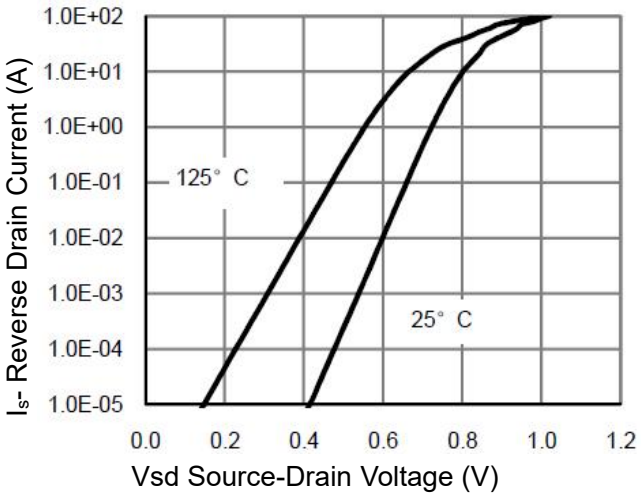


Figure 6 Source- Drain Diode Forward

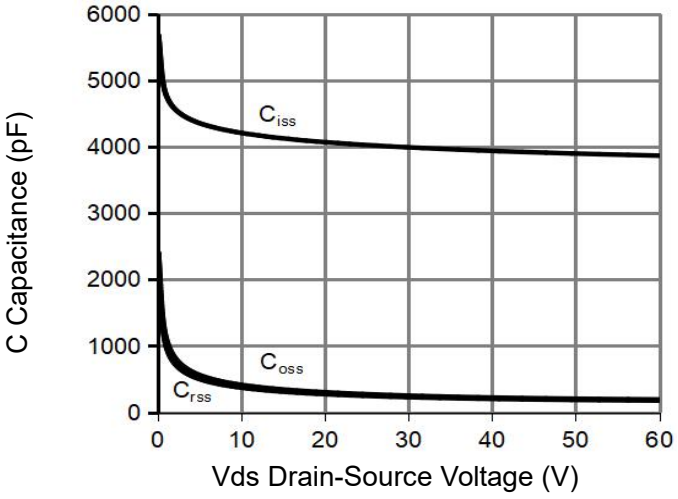


Figure 7 Capacitance vs Vds

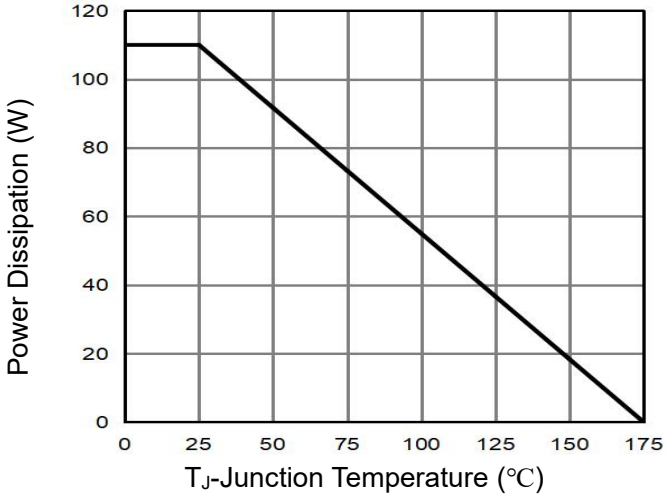


Figure 9 Power De-rating

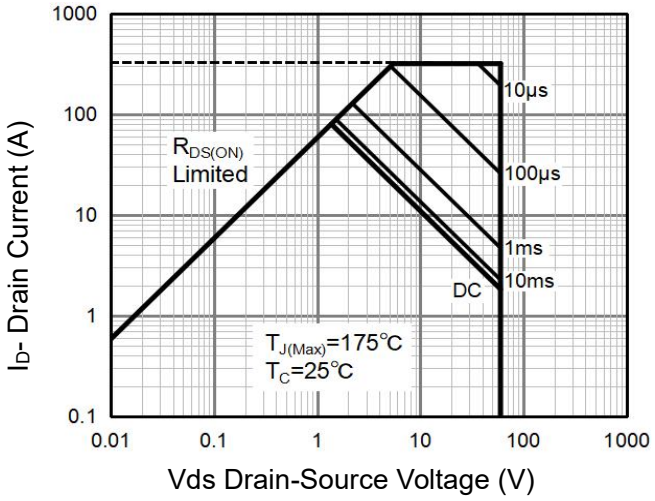


Figure 8 Safe Operation Area (Note3)

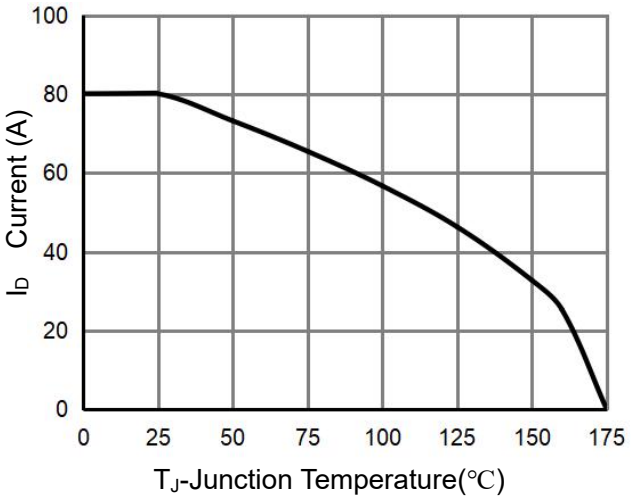


Figure 10ID Current- Junction Temperature

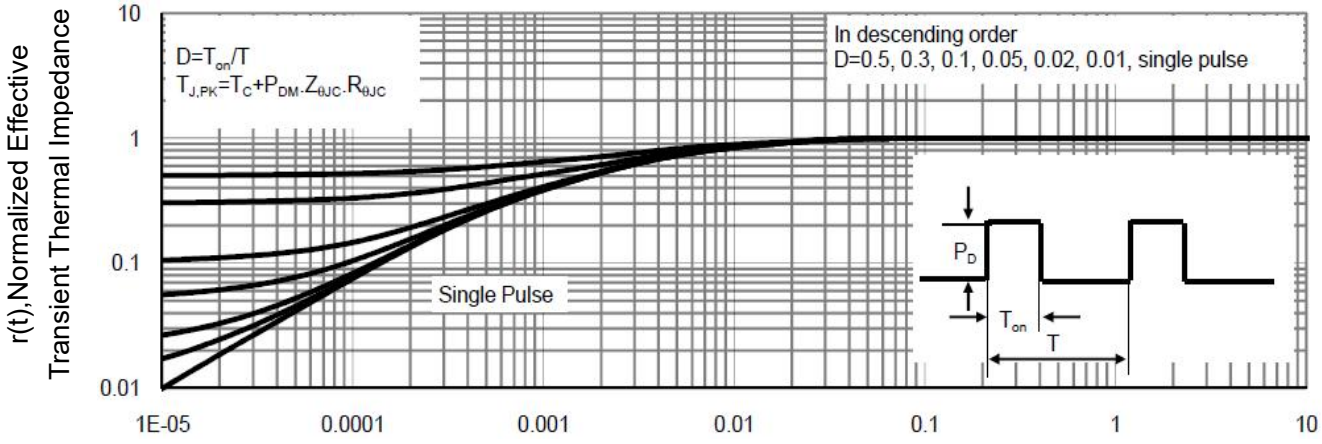
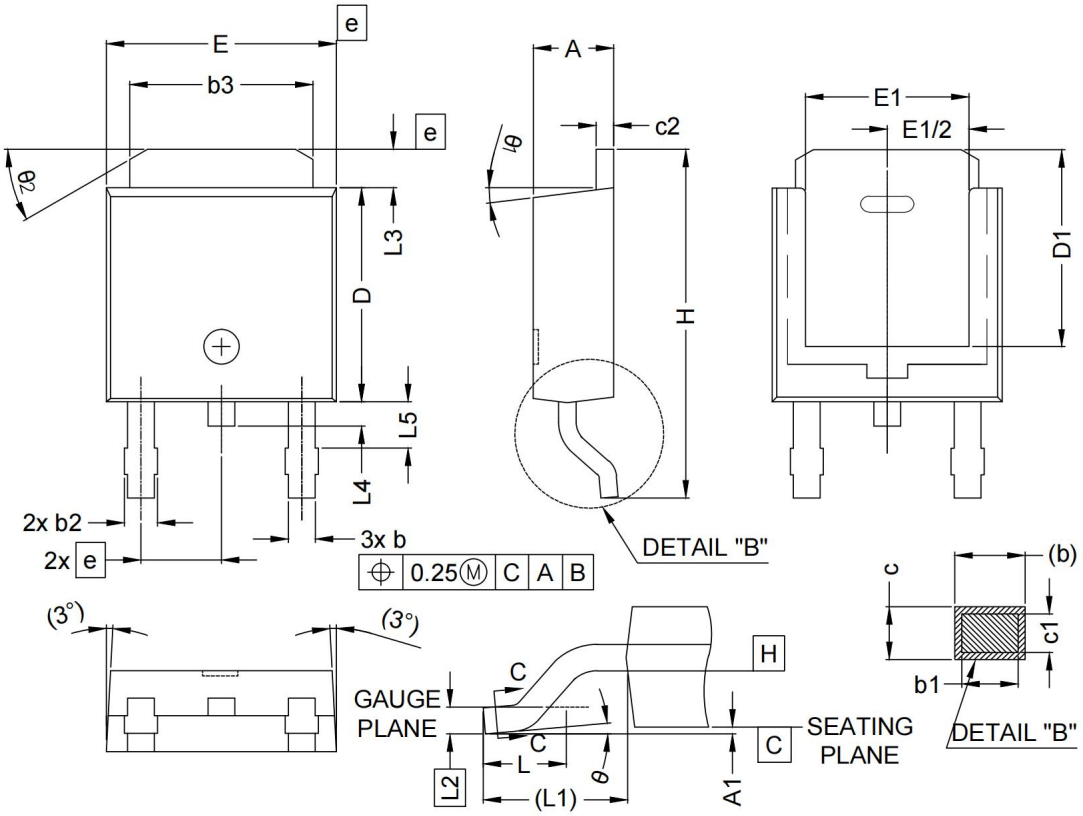


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252-2L Package Information



SYMBOL	MIN.	MAX.	SYMBOL	MIN.	MAX.	SYMBOL	MIN.	MAX.
A	2.18	2.39	E	6.35	6.73	θ1	0°	15°
A1	-	0.13	E1	4.32	-	θ2	25°	35°
b	0.65	0.89	e	2.29 BSC				
b1	0.64	0.79	H	9.94	10.34			
b2	0.76	1.13	L	1.50	1.78			
b3	4.95	5.46	L1	2.74 REF				
c	0.46	0.61	L2	0.51 BSC				
c1	0.41	0.56	L3	0.89	1.27			
c2	0.46	0.60	L4	-	1.02			
D	5.97	6.22	L5	1.14	1.49			
D1	5.21	-	θ	0°	10°			

NOTE ; 1.0 DIMENSIONING & TOLERANCEING CONFIRM TO ASME Y14.5M-1994.
2.0 ALL DIMENSIONS ARE IN MILLIMETERS. ANGLES ARE IN DEGREES.
3.0 HEAT SINK SIDE FLASH IS MAX. 0.8mm.
4.0 RADIUS ON TERMINAL IS OPTIONAL.

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